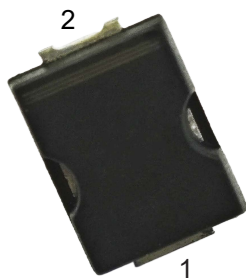


Trench MOS Barrier Schottky Rectifier

TSP10L200P6

SMP6



Features

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

Applications

- DC/DC Converters
- AC/DC Adaptors
- Switching Power Supplies
- Freewheeling Diodes

Maximum ratings and electrical characteristics (TJ = 25°C unless otherwise noted)

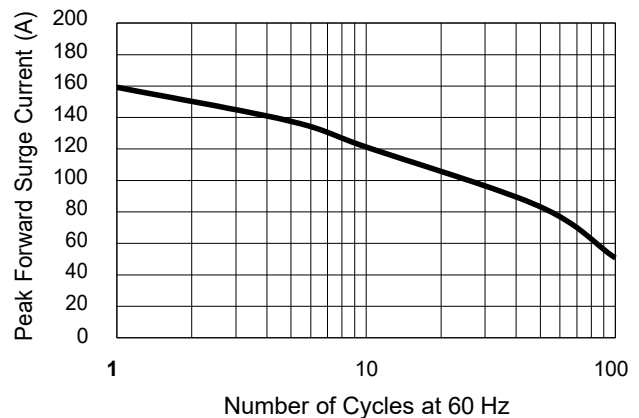
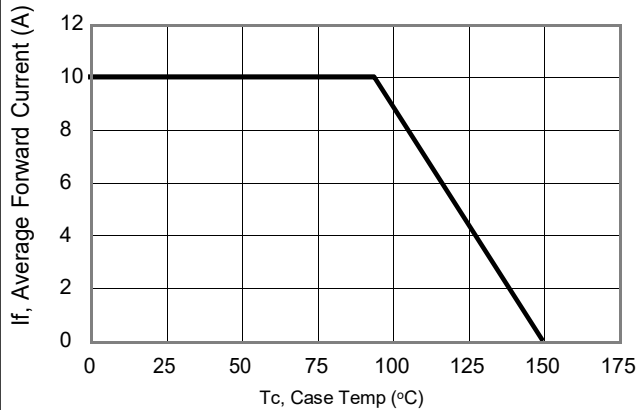
Parameter			Symbol	Limit		Unit
Maximum repetitive peak reverse voltage			VRRM	200		V
Maximum average forward rectified current			IF(AV)	10.0		A
Peak forward surge current 8.3 ms single half sine- wave superimposed on rated load per diode			IFSM	160		A
Operating junction and storage temperature range			TJ, TSTG	-55 to +150		°C
Typical thermal resistance per diode(Mounted on FR-4 PCB)			RθJC	25		°C/W
Instantaneous forward voltage per diode			VF(1)	TYP.	MAX.	V
	IF=3A	TJ=25°C		0.72	0.80	
	IF=3A	TJ=125°C		0.66	-	
	IF=10A	TJ=25°C		0.80	0.86	
	IF=10A	TJ=125°C		0.73	-	
Instantaneous reverse current per diode at rated reverse voltage		TJ=25°C	IR(2)	-	20	uA
		TJ=125°C		-	40	mA

Notes:

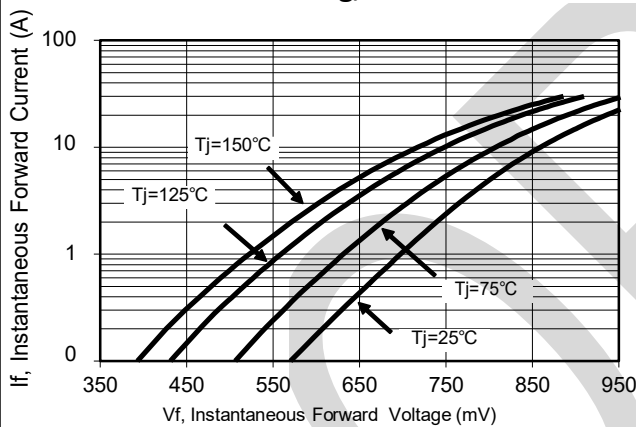
(1) Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

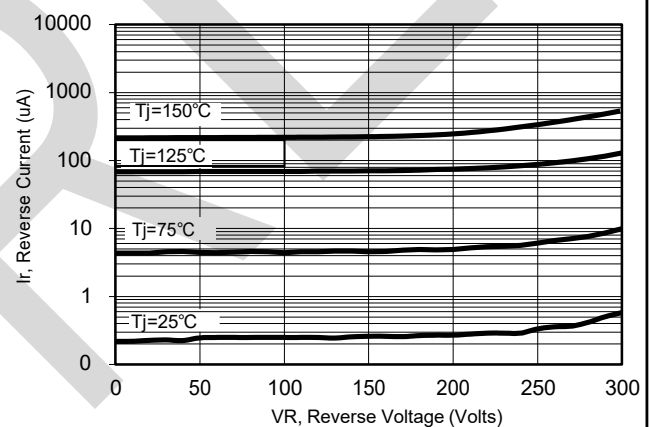
RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)



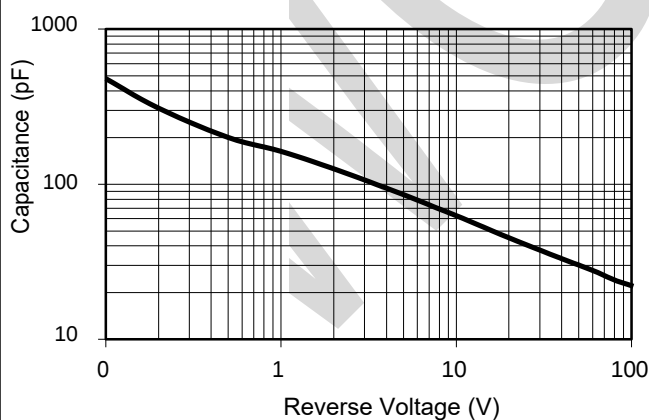
Current Derating, Case



Maximum Repetitive Surge Current



Typical Forward Voltage

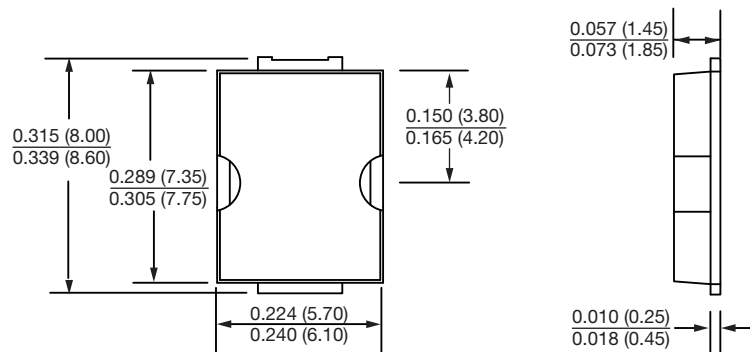


Typical Reverse Current

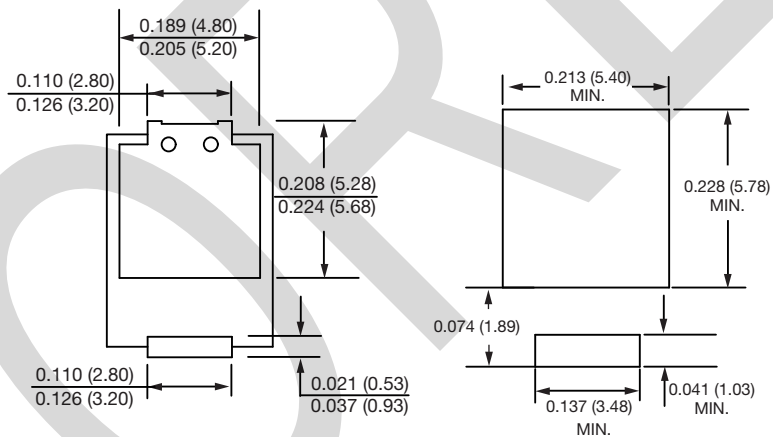
Typical Junction Capacitance

PACKAGE OUTLINE DIMENSIONS

SMP6

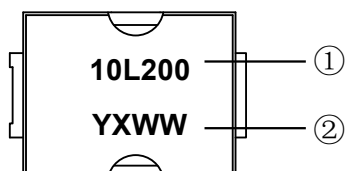


Mounting Pad Layout



Dimensions in inches and (millimeters)

Marking Information



①Product model :TSP10L200P6 Referred to as 10L200

②PDC information :

Y X WW

WW:Week code(01 to 53)

X:Internal identification code

Y:Year code(ex:0=2020)